



3LP01C-TB-H Information



For Reference Only

Part Number 3LP01C-TB-H
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 30V 100MA CP**Package**TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









3LP01C-TB-H Specifications

Manufacturer Part Number 3LPOIC-TB-H Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 100mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 1.43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7.5pF @ 10V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 250mW (Ta) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3 Report errors?		
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Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 100mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 1.43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7.5pF @ 10V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 250mW (Ta) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C100mA (Ta)Drive Voltage (Max Rds On, Min Rds On)1.5V, 4VVgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs1.43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7.5pF @ 10VVgs (Max)±10VFET Feature-Power Dissipation (Max)250mW (Ta)Rds On (Max) @ Id, Vgs10.4 Ohm @ 50mA, 4VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package3-CPPackage / CaseTO-236-3, SC-59, SOT-23-3	Package	TO-236-3, SC-59, SOT-23-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 100mA (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1.43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V 100mA (Ta) 1.5V, 4V - 1.5V - 1.5V - 1.4SnC @ 10V - 1.4SnC @ 10V - 1.5V - 1.4SnC @ 10V - 1.5V - 1.	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 100mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1.43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7.5pF @ 10V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 100mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.5V, 4V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 1.43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7.5pF @ 10V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 250mW (Ta) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 1.5V, 4V 1.43nC @ 10V 7.5pF @ 10V 7.5	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1.43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7.5pF @ 10V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	100mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 7.5pF @ 10V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 70-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	1.5V, 4V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Vgs(th) (Max) @ Id	-
Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 250mW (Ta) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	1.43nC @ 10V
FET Feature - Power Dissipation (Max) 250mW (Ta) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	7.5pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.4 Ohm @ 50mA, 4V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 70-236-3, SC-59, SOT-23-3	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs10.4 Ohm @ 50mA, 4VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package3-CPPackage / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	250mW (Ta)
Mounting Type Surface Mount Supplier Device Package Package / Case Supplier Device Package TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	10.4 Ohm @ 50mA, 4V
Supplier Device Package 3-CP Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	3-CP
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

3LP01C-TB-H Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

3LP01C-TB-H Payment Methods



















3LP01C-TB-H Shipping Methods













If you have any question about 3LP01C-TB-H, please do not hesitate to contact us!

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